

8. (Amended) A method according to claim 6, wherein the grooves are cut to a depth of from about 40 μm to about 100 μm .

10. (Amended) A method according to claim 8, wherein the depth of said grooves is controlled by process parameters including the intensity of the laser beam, the speed at which the laser beam is scanned over the grooves and the number of times the laser beam is scanned over said grooves.

12. (Amended) A method according to claim 10, wherein the average power of the laser beam is about 1.4W.

13. (Amended) A method according to claim 10, wherein the repetition rate of the laser beam is from about 2 kHz to about 5 kHz.

14. (Amended) A method according to claim 10, wherein the pulse width of the laser beam is from about 5 ns to about 30 ns.

15. (Amended) A method according to claim 10, wherein the laser beam is scanned over the second surface of the substrate from 2 to about 12 times at a velocity of about 1 mm/sec.

16. (Amended) A method according to claim 1, wherein the at least one GaN-based layer includes a plurality of GaN-based layers.

17. (Amended) A method according to claim 16, wherein the GaN-based layers are formed using epitaxial lateral overgrowth (ELOG) techniques.

18. (Amended) A laser device having cleaved facets formed according to the method of claim 1.